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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09.692,211	10/20/2000	Akihiko Ishibashi	0819-442	6705	
22204	7590 02.12.2002				
NIXON PEABODY, LLP 8180 GREENSBORO DRIVE SUITE 800			EXAMINER		
			MULPURI, SAVITRI		
MCLEAN, VA 22102			ART UNIT	PAPER NUMBER	
			2812		

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No. 09/692,211 Applicant(s)

Ishibashi et al

Examiner

Savitri Mulpuri



_		Savitri Mulpuri	2812				
	The MAILING DATE of this communication appears	on the cover sheet with the corres	pondence addı	'ess			
A SH THE	for Reply HORTENED STATUTORY PERIOD FOR REPLY IS SET MAILING DATE OF THIS COMMUNICATION.						
a - If th	ensions of time may be available under the provisions of 37 C fter SIX (6) MONTHS from the mailing date of this communic te period for reply specified above is less than thirty (30) days te considered timely.	cation,					
- If No c - Failu - Any	O period for reply is specified above, the maximum statutory ommunication. The to reply within the set or extended period for reply will, by reply received by the Office later than three months after the arned patent term adjustment. See 37 CFR 1.704(b).	y statute, cause the application to become	ome ABANDONE				
Status		2004					
				·			
		tion is non-final.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.							
	ition of Claims						
4) 💢	Claim(s) <u>1-12</u>	is/are	pending in the	e application.			
•	4a) Of the above, claim(s)	is/are	withdrawn fr	om consideration.			
5) 🗆	Claim(s)	i	s/are allowed.				
6) 💢	Claim(s) <u>1-12</u>						
7) 🗀	Claim(s)						
	Claims						
Applica	ation Papers						
9) 🗌	9) The specification is objected to by the Examiner.						
10)	The drawing(s) filed on is/are objected to by the Examiner.						
11).	The proposed drawing correction filed on is: a) approved b) disapproved.						
12)	12) The oath or declaration is objected to by the Examiner.						
	under 35 U.S.C. § 119 Acknowledgement is made of a claim for foreign pr	riority under 35 U.S.C. § 119(a)-((d).				
a) All b) Some* c) None of:							
1. Certified copies of the priority documents have been received.							
2. Certified copies of the priority documents have been received in Application No.							
	3. Copies of the certified copies of the priority do application from the International Bures ee the attached detailed Office action for a list of the	au (PCT Rule 17.2(a)).	:his National S	tage			
*See the attached detailed Office action for a list of the certified copies not received. 14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).							
Attachme		F 10011, 21122 22 212 21 21 21 21 21 21 21 21 21	,.				
		18) Interview Summary (PTO-413) Paper No	o(s).				
16) No		19) Notice of Informal Patent Application (P	•				
17) 🗀 Inf	formation Disclosure Statement(s) (PTO-1449) Paper No(s).	20) Other:					

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Art Unit:

Claim Rejections - 35 USC § 102

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-12 are rejected under 35 U.S.C. 102(b) as being anticipated by Porowski et al.

Rejection is maintained same as in paper no. 6, mailed on 8/1/01.

Applicant's arguments filed on 11/27/01 have been fully considered but they are not persuasive. Applicant amend the claims by adding vapor phase deposition. However, there is no patentable weight given to preamble language of "vapor phase deposition". Moreover, applied reference by Porowski et al discloses evaporation of the metal solution into vapor phase to deposit the first and second compound semiconductor layers of GaN (see col. 8, lines 26-40).

Applicant argues that plural steps of respectively growing plural nitride semiconductor layers on a substrate. However, Porowski et al also discloses in addition to growing first and second semiconductor layers, growing plural semiconductor layers by vapor phase techniques such as MBE or MOCVD (see col. 3, lines 61-65).

Applicant further mention that Porowski teaches a method of growing crystal by melting metals composing a group III element (Ga,Al,In) in crucible, and in nitrogen ambient when a state of equilibrium exists between vapor and solid. However, such explanation is irrelevant because the claimed limitations with claimed conditions such as pressure and temperature to grow first and second layers are met by disclosed subject matter of Porowski.

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Art Unit:

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Mulpuri whose telephone number is (703) 305-5184. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

SAVITRI MULPURI BRIMARY EXAMINER